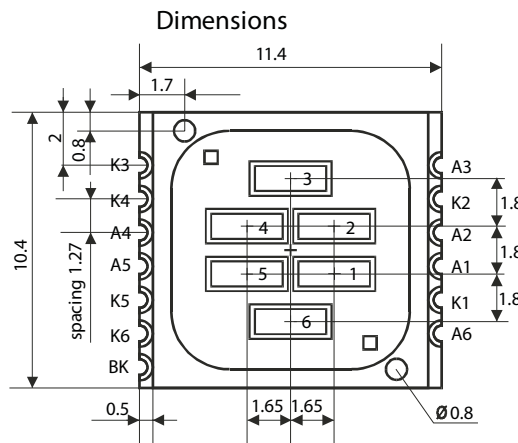
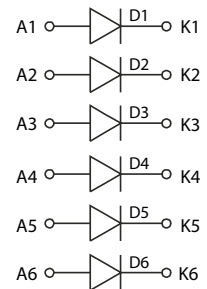


FEATURES

- High responsivity
- Low capacitance
- Suitable for SMT
- High reliability
- Peak wavelength at 830 nm



Schematic



DESCRIPTION

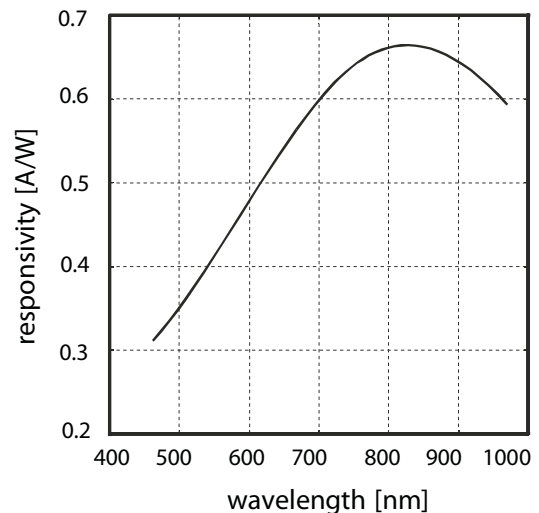
The photosensor is made of 6-chip photodiode array. Photodiodes are produced in planar technology and passivated with antireflective layer of silicon-nitride. Photodiodes are bonded to the PCB and protected with transparent epoxy glue. The photodiode can work in photovoltaic or photoconductive mode.

TEMPERATURE CONDITIONS

Storage	-35 °C..+125 °C
Operating	-20 °C..+80 °C

PRODUCT OPTIONS

Type	Photodiode type
PA2100A	FD3113
PA2100B	FD2712
PA2100C	FD2311
PA2100D	FD2309



PHOTODIODE CHARACTERISTICS

DIODE TYPE	DIMENSIONS		ELECTRICAL PARAMETERS				OPTICAL PARAMETERS		
	CHIP SIZE (mm)	ACTIVE AREA (mm ²)	DARK CURRENT	BV	CAPACITANCE		PEAK	RESPONSE	CURRENT ¹
			V _r = -5V	I _r > -50 μA	V _r = 0V	V _r = -5V	I		I _{sc}
			TYP	MIN	TYP	TYP	TYP	TYP	TYP
(nA)	(V)	(pF)	(pF)	(nm)	(A/W)	(μA)			
FD 3113	3.1 x 1.3	3.10	<1	50	52	23	830	0.67	1000
FD 2712	2.7 x 1.2	2.50	<1	50	35	20	830	0.67	830
FD 2311	2.3 x 1.1	1.90	<1	50	35	16	830	0.67	670
FD 2309	2.3 x 0.9	1.46	<1	50	22	10	830	0.67	520

Note 1: CURRENT (I_{sc}) is measured under 100 mW/cm² AM spectrum.